

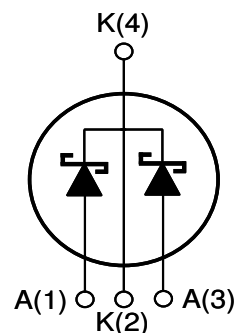
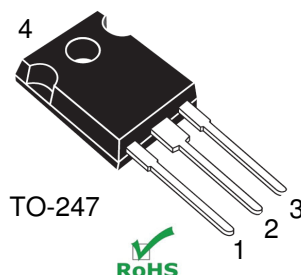
## Silicon Carbide Power Schottky Diode

### Features:

- Positive Temperature Coefficient for Ease of Paralleling
- Temperature Independent Switching Behavior
- 175 °C Maximum Operating Temperature
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage

### Applications:

- Solar Inverter
- SMPS
- Power Factor Correction
- Induction Heating
- UPS
- Motor Drive



Internal Schematic

Product Summary		
$V_{DC}$	1200	V
$I_F$	60	A
$Q_c$	260	nC

## MAXIMUM RATINGS

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_j = 25\text{ °C}$	1200	V
DC Blocking Voltage	$V_{DC}$		1200	
Continuous Forward Current (Per Leg / Per Device)	$I_F$	$T_C < 145\text{ °C}$	30 / 60	A
		$T_C < 100\text{ °C}$	45 / 90	
Peak Repetitive Forward Current	$I_{FRM}$	$T_C = 125\text{ °C}, D = 0.1$	120	
Non-Repetitive Forward Surge Current (Per Leg / Per Device)	$I_{FSM}$	$T_C = 25\text{ °C}, t_p = 10\text{ ms}$	110 / 220	
		$T_C = 25\text{ °C}, t_p = 10\text{ us}$	700 / 1400	
Power Dissipation (Per Leg / Per Device)	$P_{TOT}$	$T_C = 25\text{ °C}$	300 / 600	W
Operating and Storage Temperature	$T_j, T_{stg}$		-55 to +175	°C

**THERMAL CHARACTERISTICS (Per Leg)**

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Thermal Resistance, junction-case	$R_{th JC}$	Per Legs	-	0.5	-	°C / W
		Both Legs	-	0.25	-	
Thermal Resistance, junction-ambient	$R_{th JA}$		-	62	-	

**ELECTRICAL CHARACTERISTICS (Per Leg), at  $T_j = 25\text{ C}$  unless otherwise stated**

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Forward Voltage	$V_F$	$I_F = 30\text{ A}, T_j = 25\text{ °C}$	-	1.6	1.8	V
		$I_F = 30\text{ A}, T_j = 175\text{ °C}$	-	2.4	2.9	
Reverse Current	$I_R$	$V_R = 1200\text{ V}, T_j = 25\text{ °C}$	-	30	300	uA
		$V_R = 1200\text{ V}, T_j = 175\text{ °C}$	-	600	-	
Total Capacitive Charge	$Q_C$	$V_R = 400\text{ V}, I_F = 30\text{ A}, di/dt = 500\text{ A/us}$	-	130	-	nC
Total Capacitance	C	$V_R = 1\text{ V}, f = 100\text{ kHz}$	-	3690	-	pF
		$V_R = 300\text{ V}, f = 100\text{ kHz}$	-	152	-	
		$V_R = 600\text{ V}, f = 100\text{ KHz}$	-	106	-	

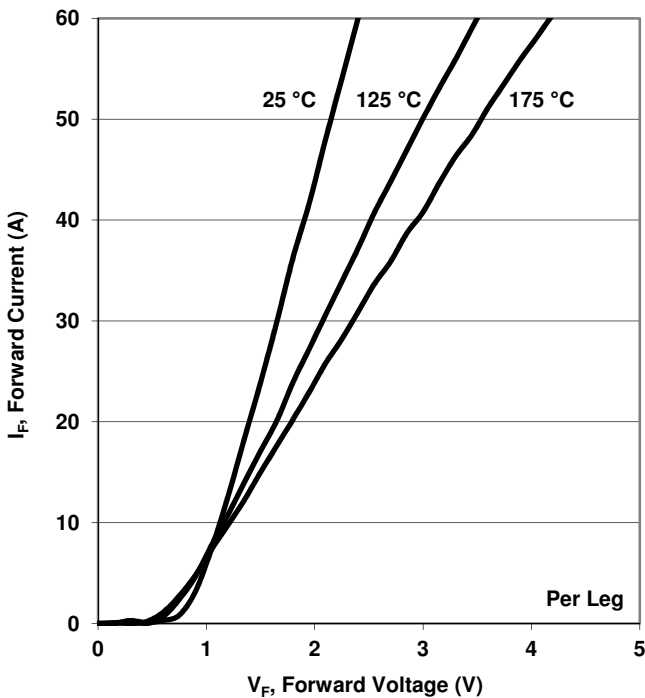


Figure 1. Typ. Forward Characteristics  
 $I_F = f(V_F)$ ; parameter:  $T_j$

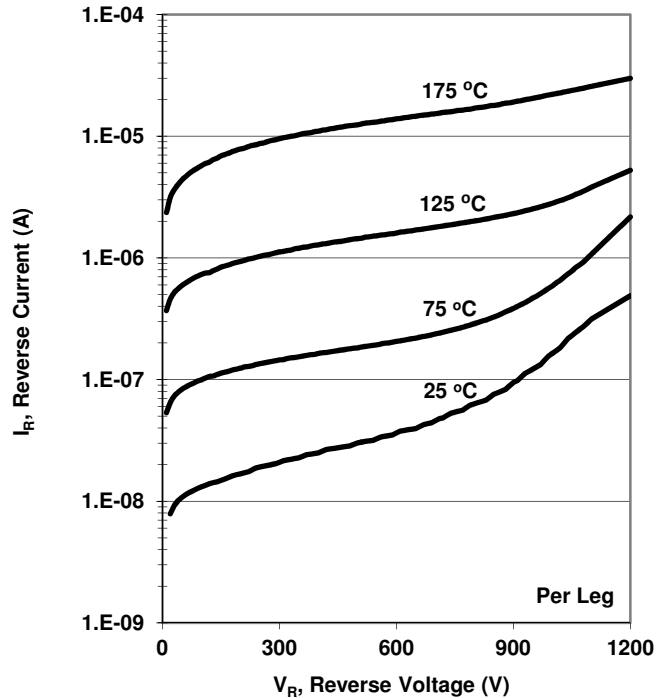


Figure 2. Typ. Reverse Characteristics  
 $I_R = f(V_R)$

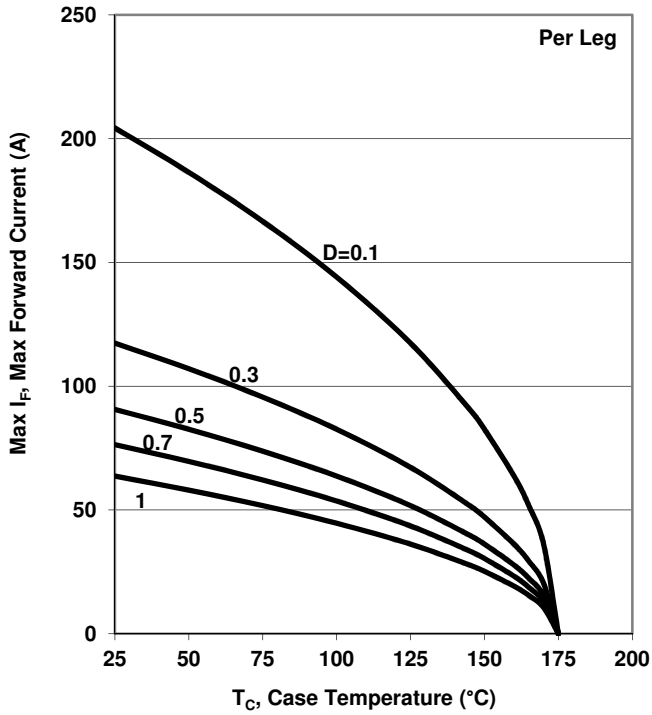


Figure 3. Max Forward Current  
 $I_F = f(T_C); T_j < 175\text{ }^\circ\text{C}; R_{th,jc(max)}$

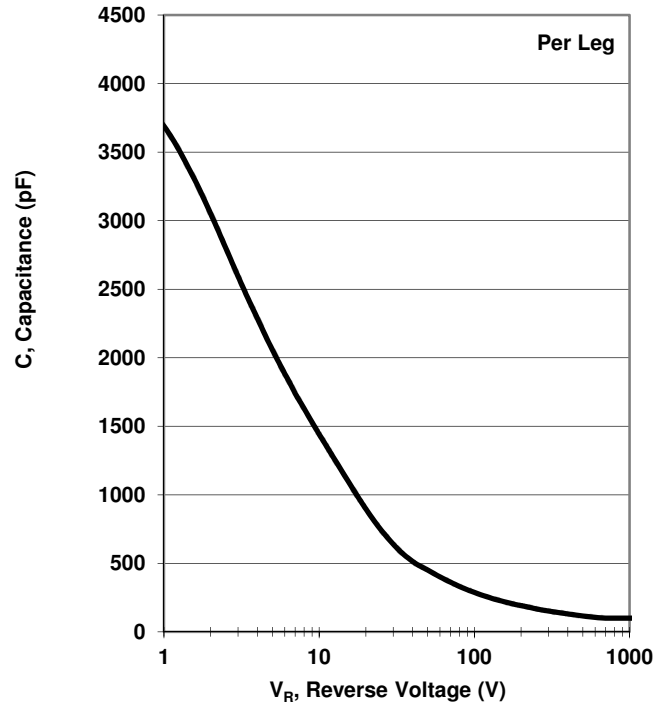
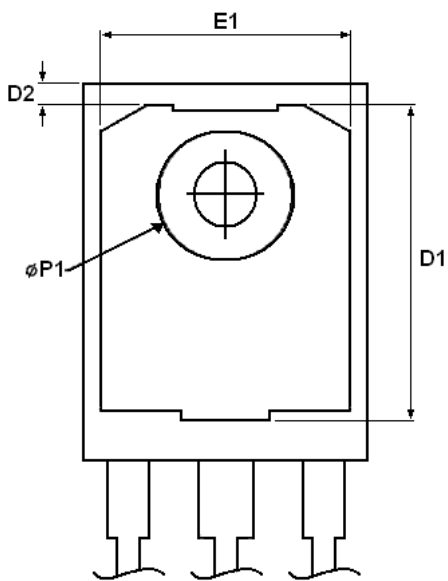
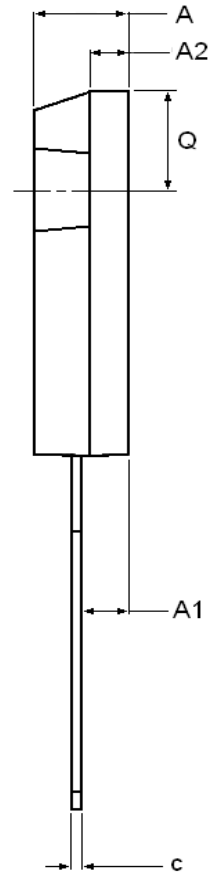
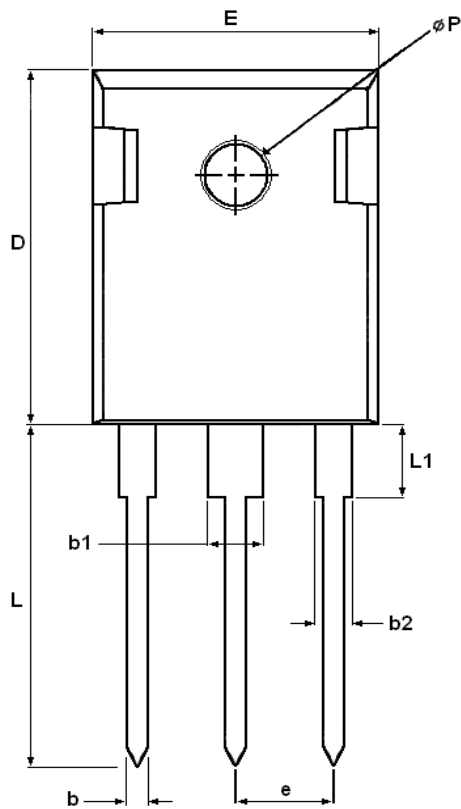


Figure 4. Typ. Capacitance vs. Reverse Voltage  
 $C = f(V_R); T_C = 25\text{ }^\circ\text{C}; f = 1\text{ MHz}$

**Package Dimensions: TO-247**



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.903	5.157	0.193	0.203
A1	2.273	2.527	0.090	0.100
A2	1.853	2.108	0.073	0.083
b	1.073	1.327	0.042	0.052
b1	2.873	3.381	0.113	0.133
b2	1.903	2.386	0.042	0.052
c	0.600	0.752	0.024	0.029
D	20.823	21.077	0.820	0.830
D1	17.393	17.647	0.685	0.695
D2	1.063	1.317	0.042	0.052
e	5.450		0.215	
E	15.773	16.027	0.621	0.631
E1	13.893	14.147	0.547	0.557
L	20.053	20.307	0.789	0.799
L1	4.168	4.472	0.165	0.175
Q	6.043	6.297	0.238	0.248
ØP	3.560	3.660	0.140	0.144
ØP1	7.063	7.317	0.278	0.288

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